

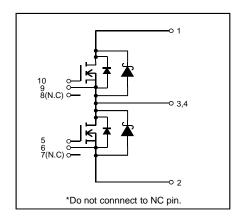
Application

- · Motor drive
- · Inverter, Converter
- · Photovoltaics, wind power generation.
- · Induction heating equipment.

Features

- 1) Low surge, low switching loss.
- 2) High-speed switching possible.
- 3) Reduced temperature dependence.

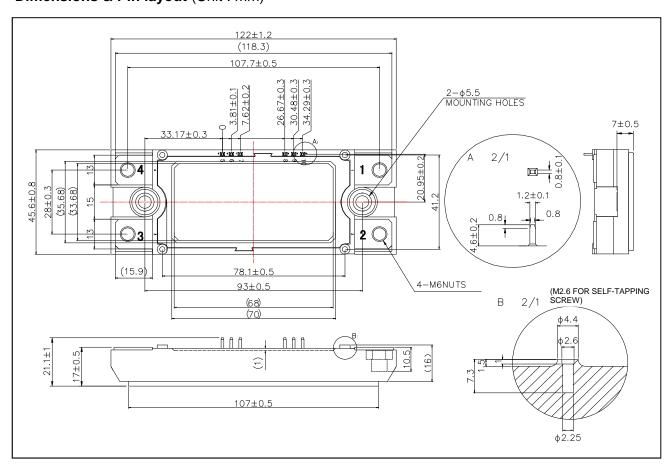
●Circuit diagram



Construction

This product is a half bridge module consisting of SiC-DMOS and SiC SBD from ROHM.

●Dimensions & Pin layout (Unit : mm)



● Absolute maximum ratings (Tj = 25°C)

Parameter	Symbol	Conditions	Limit	Unit
Drain-source voltage	V_{DSS}	G-S short	1200	V
Gate-source voltage(+)	W	D-S short	22	V
Gate-source voltage(-)	V_{GSS}	D-3 SHOIL	-6	V
Drain current *1	I _D	DC(Tc=60°C)	120	Α
	I _{DRM}	Pulse (Tc=60°C) 1ms *2	240	Α
Source current *1	I _S	Tc=60°C	120	Α
	I _{SRM}	Pulse (Tc=60°C) 1ms *2	240	Α
Total power disspation *3	Ptot	Tc=25°C	780	W
Junction temperature	Tj		-40 to150	°C
Storage temperature	Tstg		-40 to125	°C
Isolation voltage*4	Visol	Terminals to baseplate, f=60Hz AC 1min.	2500	Vrms
Mounting torque	ı	Main Terminals : M6 screw	4.5	N · m
		Mounting to heat shink: M5 screw	3.5	N · m

^(*1) Measurement of Tc is to be done at the point just under the chip.

●Electrical characteristics (Tj=25°C)

Parameter	Symbol	Conditions		Min.	Тур.	Max.	Unit
Static drain-source on-state voltage	V _{DS(on)}	I _D =120A, V _{GS} =18V	Tj=25°C	_	2.4	3.2	V
			Tj=125°C	_	3.5	4.6	V
Drain cutoff current	I _{DSS}	V _{DS} =1200V, V _{GS} =0V			ı	2	mA
Source-drain voltage	V_{SD}	V _{GS} =0V, I _S =120A	Tj=25°C	-	1.7	2.1	V
			Tj=125°C	-	2.2	2.7	V
Gate-source threshold voltag	$V_{GS(th)}$	V _{DS} =10V, I _D =22mA	1.6	2.7	4.0	V	
Gate-source leakage current	I _{GSS}	V _{GS} =22V, V _{DS} =0V		_	_	0.5	μΑ
		$V_{GS} = -6V, V_{DS} = 0V$		-0.5	_	_	μΑ
Switching characteristics	td(on)	$V_{GS(on)}$ =18V, $V_{GS(off)}$ =0V		_	45	_	ns
	tr	V _{DS} =600V	-	50	_	ns	
	trr	I _D =120A	-	30	_	ns	
	td(off)	R_G =3.9 Ω inductive load		-	170	_	ns
	tr			_	60	_	ns
Input capacitance	Ciss	V _{DS} =10V, V _{GS} =0V, f=1MHz		-	14	_	nF
Junction-to-case thermal resistance	Rth(j-c)	DMOS (1/2 module) *5		_	1	0.16	°C/W
		SBD (1/2 module) *5		-	_	0.21	°C/W
Case-to-heat sink Thermal resistance	Rth(c-f)	Case to heat sink, per 1 Thermal grease appied	_	0.04	_	°C/W	

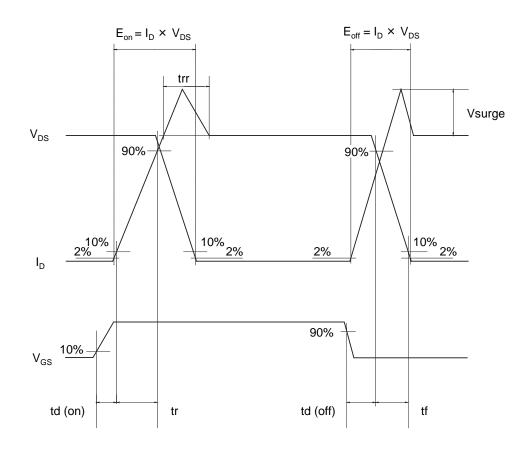
^(*5) Measurement of Tc is to be done at the point just beneath the chip.

^(*2) Repetition rate should be kept within the range where temperature rise of die should not exceed Tj max.

^(*3) Tj is less than 150°C (*4) Actual measurement is 3000V/1sec . in accordance with UL1557.

^(*6) Typical value is measured by using thermally conductive grease of λ =0.9W / (m · K).

Waveform for switching test



●Electrical characteristic curves (Typical)

Fig.1 Typical Output Characteristics

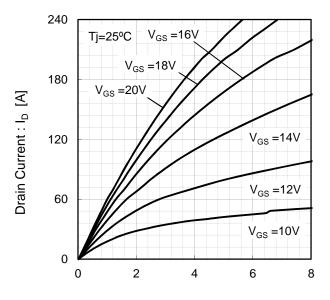
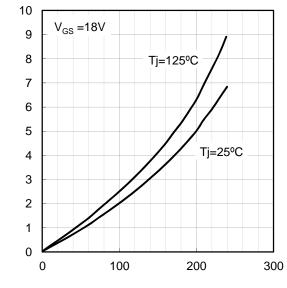


Fig.2 Drain-Source Voltage vs. Drain Current

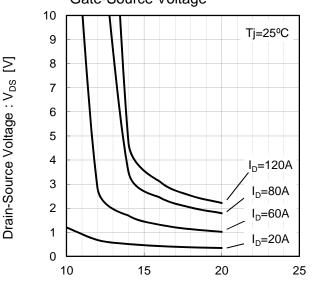


Drain-Source Voltage: V_{DS} [V]

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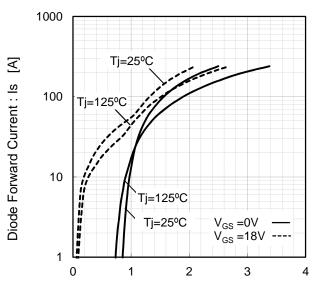
Drain Current : I_D [A]

Fig.3 Drain-Source Voltage vs. Gate-Source Voltage



Gate-Source Voltage : V_{GS} [V]

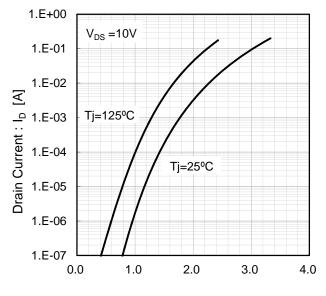
Fig.4 Forward characteristic of Diode-inverter



Source-Drain Voltage: V_{SD} [V]

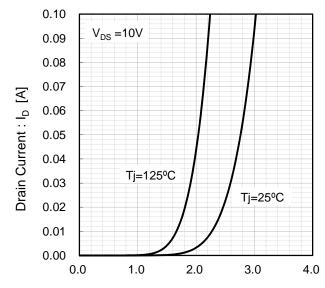
● Electrical characteristic curves (Typical)

Fig.5 Drain Current vs. Gate-Source Voltage



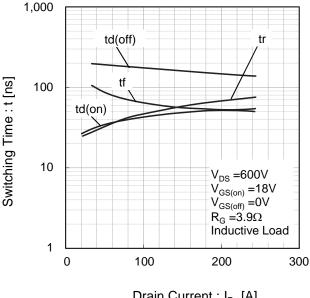
Gate-Source Voltage : V_{GS} [V]

Fig.6 Drain Current vs. Gate-Source Voltage



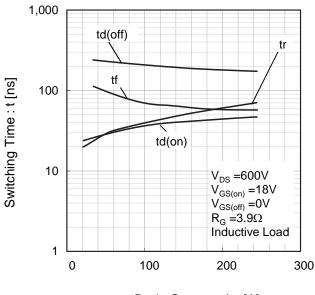
Gate-Source Voltage : V_{GS} [V]

Fig.7 Switching Characteristics [Tj=25°C]



Drain Current : I_D [A]

Fig.8 Switching Characteristics [Tj=125°C]



Drain Current : I_D [A]

• Electrical characteristic curves (Typical)

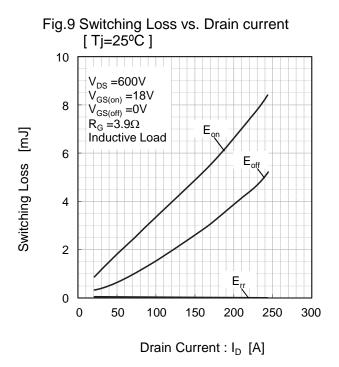
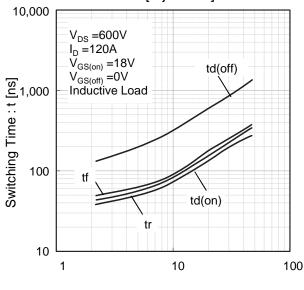


Fig.10 Switching Loss vs. Drain current [Tj=125°C] 10 V_{DS} =600V $-V_{GS(on)} = 18V$ $-V_{GS(off)} = 0V$ $-R_G = 3.9\Omega$ Switching Loss [mJ] Inductive Load 6 4 $\mathsf{E}_{\mathrm{off}}$ 2 E_{rr} 0 100 200 300 Drain Current: I_D [A]

Fig.11 Reverse Recovery Characteristics vs. Fig.12 Reverse Recovery Characteristics vs. Drain Current [Tj=125°C] Drain Current [Tj=25°C] 100 100 100 100 trr trr Reverse Recovery Current : Irr [A] Reverse Recovery Current : Irr [A] Reverse Recovery Time : trr [ns] Reverse Recovery Time: trr Irr Irr 10 10 V_{DS} =600V V_{DS} =600V $V_{GS(on)} = 18V$ $V_{GS(off)} = 0V$ $R_G = 3.9\Omega$ $V_{GS(on)} = 18V$ $V_{GS(off)} = 0V$ $R_G = 3.9\Omega$ Inductive Load Inductive Load 0 100 300 100 300 200 0 200 Drain Current : I_D [A] Drain Current : I_D [A]

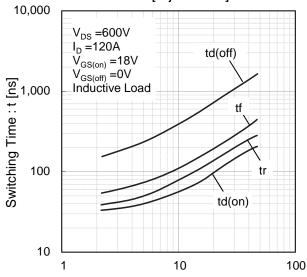
●Electrical characteristic curves (Typical)

Fig.13 Switching Characteristics vs. Gate Resistance [Tj=25°C]



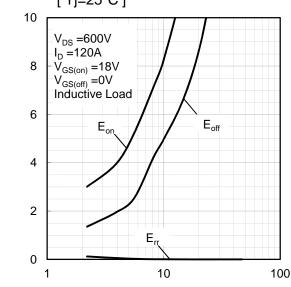
Gate Resistance : R_G [Ω]

Fig.14 Switching Characteristics vs. Gate Resistance [Tj=125°C]



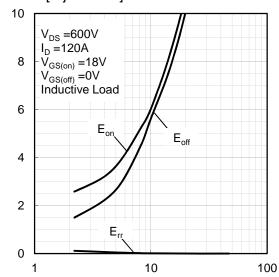
Gate Resistance : R_G [Ω]

Fig.15 Switching Loss vs. Gate Resistance [Tj=25°C]



Gate Resistance : R_G [Ω]

Fig.16 Switching Loss vs. Gate Resistance [Tj=125°C]



Gate Resistance : R_G [Ω]

Switching Loss [mJ]

●Electrical characteristic curves (Typical)

Fig.17 Typical Capacitance vs. Drain-Source Voltage 100 C_{iss} 10 Capasitance: C [nF] C_{oss} 1 0.1 Tj=25°C C_{rss} f = 1MHz $V_{GS} = 0V$ 0.01 100 0.01

[Tj=25°C]

25

I_D=120A

V_{DD}=600V

Pulsed

15

0
0
200
400
600
800

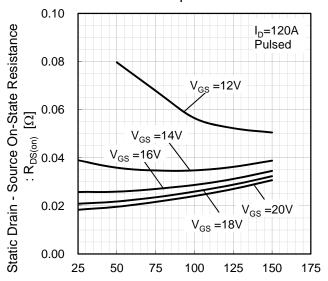
Fig.18 Gate Charge Characteristics

Drain-Source Voltage : V_{DS} [V]

Fig.19 Normalized Transient Thermal Impedance vs. Pulse Width 10 Normalized Transient Thermal Impedance: Rth Single Pulse Tc=25°C 1 Per unit base DMOS part: Rth(j-c)=0.16°C/W SBD part : Rth(j-c)=0.21°C/W 0.1 0.001 0.01 0.1 10 Pulse Width: Pw [s]

Fig.20 Static Drain - Source On-State Resistance vs. Junction Temperature

Total Gate charge: Qg [nC]



Junction Temperature : Tj [°C]

Notes

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